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μA741

FREQUENCY-COMPENSATED OPERATIONAL AMPLIFIER

FAIRCHILD LINEAR INTEGRATED CIRCUITS

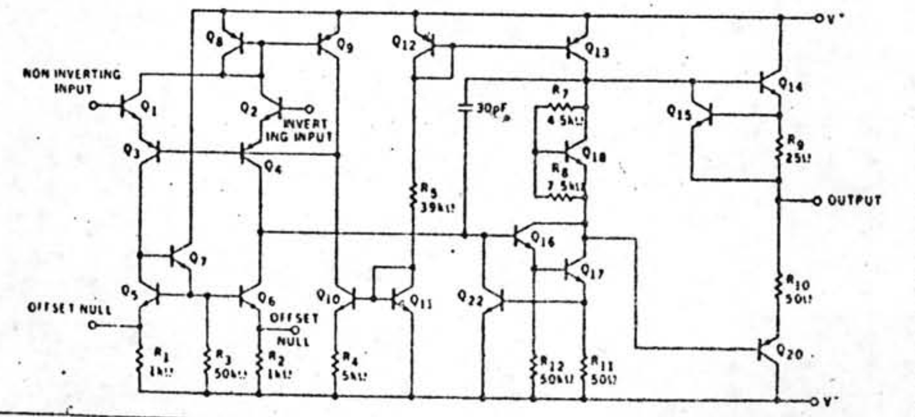
GENERAL DESCRIPTION – The μA741 is a high performance monolithic operational amplifier constructed on a single silicon chip, using the Fairchild Planar* epitaxial process. It is intended for a wide range of analog applications. High common mode voltage range and absence of "latch-up" tendencies make the μA741 ideal for use as a voltage follower. The high gain and wide range of operating voltage provides superior performance in integrator, summing amplifier, and general feedback applications.

- NO FREQUENCY COMPENSATION REQUIRED
- SHORT-CIRCUIT PROTECTION
- OFFSET VOLTAGE NULL CAPABILITY
- LARGE COMMON-MODE AND DIFFERENTIAL VOLTAGE RANGES
- LOW POWER CONSUMPTION
- NO LATCH UP

ABSOLUTE MAXIMUM RATINGS

Supply Voltage	
Military (312 Grade)	±22 V
Commercial (393 Grade)	±18 V
Internal Power Dissipation (Note 1)	
Metal Can	500 mW
Ceramic DIP	670 mW
Silicone DIP	340 mW
Mini DIP	310 mW
Flatpak	570 mW
Differential Input Voltage	±30 V
Input Voltage (Note 2)	±15 V
Storage Temperature Range	
Metal Can, Ceramic DIP, and Flatpak	−65°C to +150°C
Mini DIP and Silicon DIP	−55°C to +125°C
Operating Temperature Range	
Military (312 Grade)	−55°C to +125°C
Commercial (393 Grade)	0°C to + 70°C
Lead Temperature (Soldering)	
Metal Can, Ceramic DIP and Flatpak (60 seconds)	300°C
Mini DIP and Silicone DIP (10 seconds)	260°C
Output Short Circuit Duration (Note 3)	Indefinite

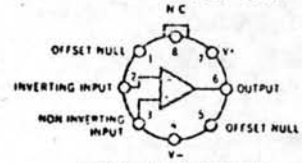
EQUIVALENT CIRCUIT



Notes on following pages.

CONNECTION DIAGRAMS (TOP VIEW)

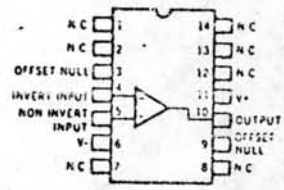
8 LEAD METAL CAN



NOTE PIN 4 CONNECTED TO CASE

ORDER PART NOS.
U5B7741312
U5B7741393

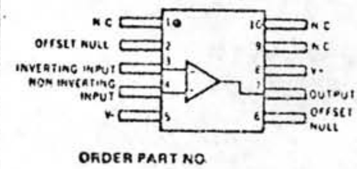
14 LEAD DIP



FOR CERAMIC DIP ORDER PART NOS.
U6A7741312
U6A7741393

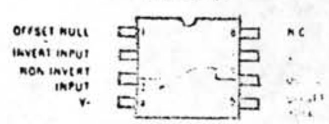
FOR SILICONE DIP ORDER PART NO.:
U9A7741393

FLATPACK



ORDER PART NO.
U3F7741312

MINIDIP



ORDER PART NO.
U9T7741393

*Planar is a patented Fairchild process.

83

312 GRADE

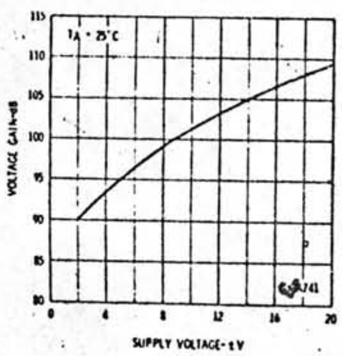
ELECTRICAL CHARACTERISTICS ($V_S = \pm 15$ V, $T_A = 25°C$ unless otherwise specified)

PARAMETERS (see definitions)	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Offset Voltage	$R_S \leq 10$ kΩ		1.0	5.0	mV
Input Offset Current			20	200	nA
Input Bias Current			80	500	nA
Input Resistance		0.3	2.0		MΩ
Input Capacitance			1.4		pF
Offset Voltage Adjustment Range			±15		mV
Large-Signal Voltage Gain	$R_L \geq 2$ kΩ, $V_{out} = \pm 10$ V	50,000	200,000		
Output Resistance			75		Ω
Output Short-Circuit Current			25		mA
Supply Current			1.7	2.8	mA
Power Consumption			50	85	mW
Transient Response (unity gain)	$V_{in} = 20$ mV, $R_L = 2$ kΩ, $C_L \leq 100$ pF				
Risetime			0.3		μs
Overshoot			5.0		%
Slew Rate	$R_L \geq 2$ kΩ		0.5		V/μs
The following specifications apply for $-55°C \leq T_A \leq +125°C$:					
Input Offset Voltage	$R_S \leq 10$ kΩ		1.0	6.0	mV
Input Offset Current	$T_A = +125°C$		7.0	200	nA
	$T_A = -55°C$		85	500	nA
Input Bias Current	$T_A = +125°C$		0.03	0.5	μA
	$T_A = -55°C$		0.3	1.5	μA
Input Voltage Range		±12	±13		V
Common Mode Rejection Ratio	$R_S \leq 10$ kΩ	70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10$ kΩ		30	150	μV/V
Large-Signal Voltage Gain	$R_L \geq 2$ kΩ, $V_{out} = \pm 10$ V	25,000			
Output Voltage Swing	$R_L \geq 10$ kΩ	±12	±14		V
	$R_L \geq 2$ kΩ	±10	±13		V
Supply Current	$T_A = +125°C$		1.5	2.5	mA
	$T_A = -55°C$		2.0	3.3	mA
Power Consumption	$T_A = +125°C$		45	75	mW
	$T_A = -55°C$		60	100	mW

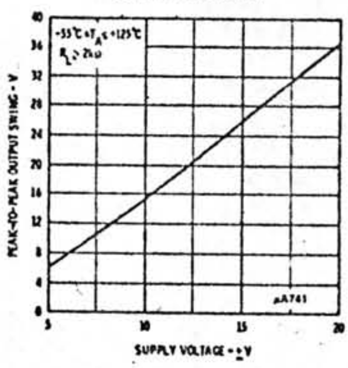
TYPICAL PERFORMANCE CURVES

312 GRADE

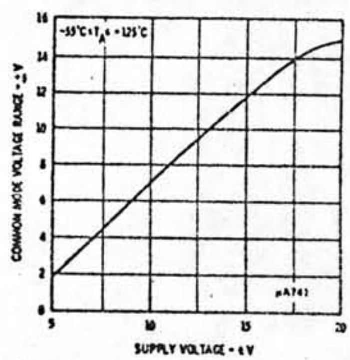
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF SUPPLY VOLTAGE



OUTPUT VOLTAGE SWING AS A FUNCTION OF SUPPLY VOLTAGE



INPUT COMMON MODE VOLTAGE RANGE AS A FUNCTION OF SUPPLY VOLTAGE



393 GRADE

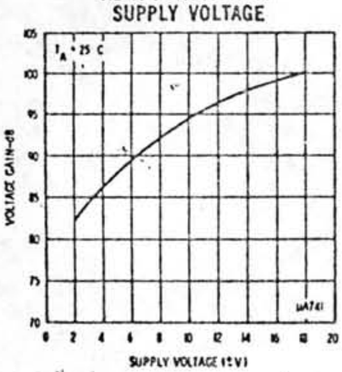
ELECTRICAL CHARACTERISTICS ($V_S = \pm 15$ V, $T_A = 25°C$ unless otherwise specified)

PARAMETERS (see definitions)	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Offset Voltage	$R_S \leq 10$ kΩ		2.0	6.0	mV
Input Offset Current			20	200	nA
Input Bias Current			80	500	nA
Input Resistance		0.3	2.0		MΩ
Input Capacitance			1.4		pF
Offset Voltage Adjustment Range			±15		mV
Input Voltage Range		±12	±13		V
Common Mode Rejection Ratio	$R_S \leq 10$ kΩ	70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10$ kΩ		30	150	μV/V
Large-Signal Voltage Gain	$R_L \geq 2$ kΩ, $V_{out} = \pm 10$ V	20,000	200,000		
Output Voltage Swing	$R_L \geq 10$ kΩ	±12	±14		V
	$R_L \geq 2$ kΩ	±10	±13		V
Output Resistance			75		Ω
Output Short-Circuit Current			25		mA
Supply Current			1.7	2.8	mA
Power Consumption			50	85	mW
Transient Response (unity gain)	$V_{in} = 20$ mV, $R_L = 2$ kΩ, $C_L \leq 100$ pF				
Risetime			0.3		μs
Overshoot			5.0		%
Slew Rate	$R_L \geq 2$ kΩ		0.5		V/μs
The following specifications apply for $0°C \leq T_A \leq +70°C$:					
Input Offset Voltage				7.5	mV
Input Offset Current				300	nA
Input Bias Current				800	nA
Large-Signal Voltage Gain	$R_L \geq 2$ kΩ, $V_{out} = \pm 10$ V	15,000			
Output Voltage Swing	$R_L \geq 2$ kΩ	±10	±13		V

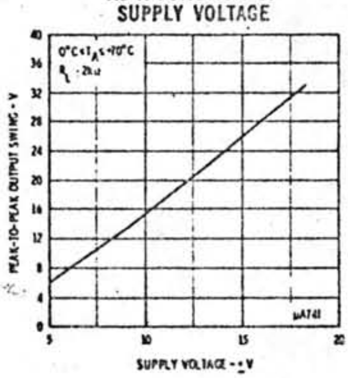
TYPICAL PERFORMANCE CURVES

393 GRADE

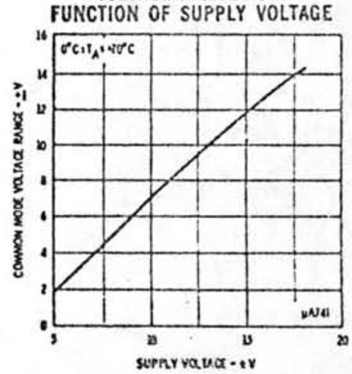
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF SUPPLY VOLTAGE



OUTPUT VOLTAGE SWING AS A FUNCTION OF SUPPLY VOLTAGE



INPUT COMMON MODE VOLTAGE RANGE AS A FUNCTION OF SUPPLY VOLTAGE

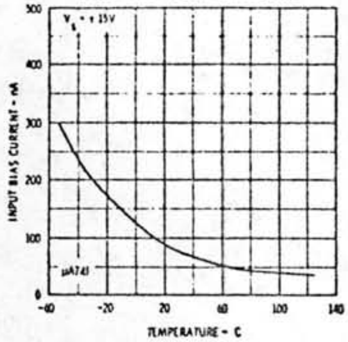


NOTES

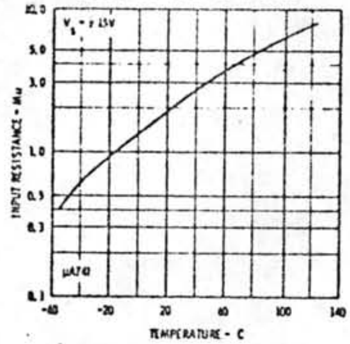
1. Rating applies to ambient temperatures up to 70°C. Above 70°C ambient derate linearly at 6.3 mW/°C for the Metal Can, 8.3 mW/°C for the Ceramic DIP, 6.3 mW/°C for the Silicone DIP, 5.6 mW/°C for the Mini DIP and 7.1 mW/°C for the Flatpak.
2. For supply voltages less than ±15 V, the absolute maximum input voltage is equal to the supply voltage.
3. Short circuit may be to ground or either supply. Rating applies to + 125°C case temperature or 75°C ambient temperature.

TYPICAL PERFORMANCE CURVES (312 GRADE)

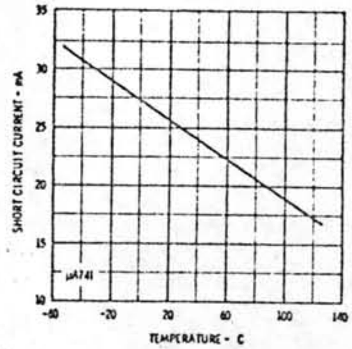
INPUT BIAS CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



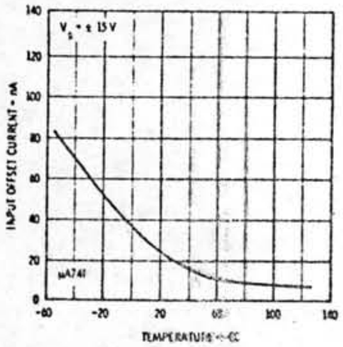
INPUT RESISTANCE AS A FUNCTION OF AMBIENT TEMPERATURE



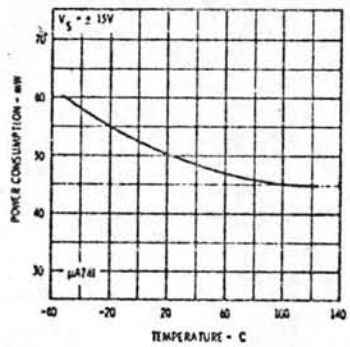
OUTPUT SHORT-CIRCUIT CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



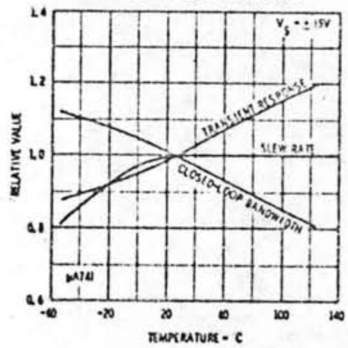
INPUT OFFSET CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



POWER CONSUMPTION AS A FUNCTION OF AMBIENT TEMPERATURE

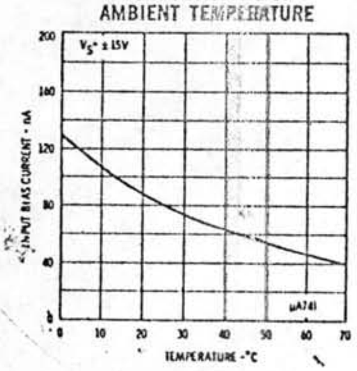


FREQUENCY CHARACTERISTICS AS A FUNCTION OF AMBIENT TEMPERATURE

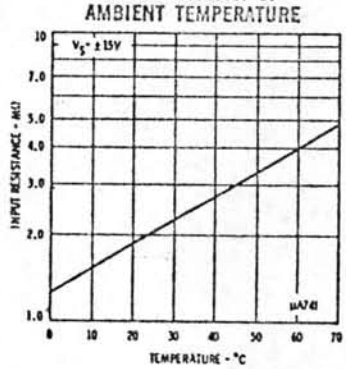


(393 GRADE)

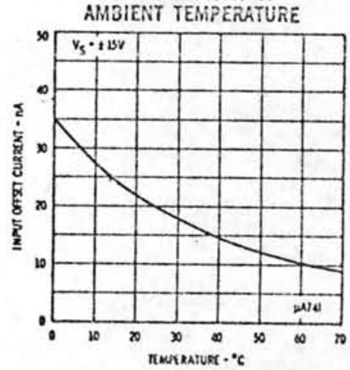
INPUT BIAS CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



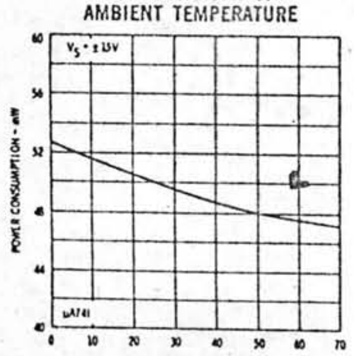
INPUT RESISTANCE AS A FUNCTION OF AMBIENT TEMPERATURE



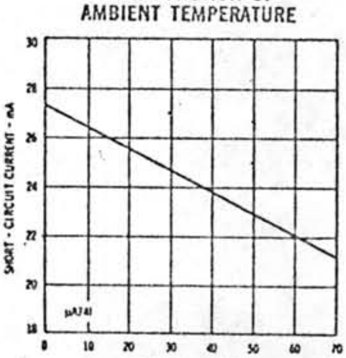
INPUT OFFSET CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



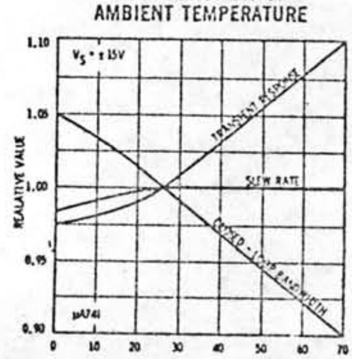
POWER CONSUMPTION AS A FUNCTION OF AMBIENT TEMPERATURE



OUTPUT SHORT-CIRCUIT CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE

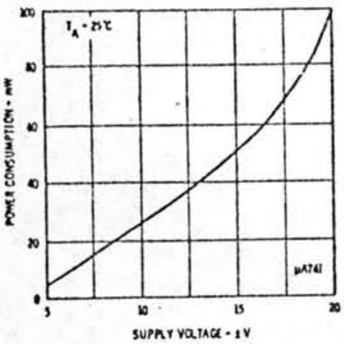


FREQUENCY CHARACTERISTICS AS A FUNCTION OF AMBIENT TEMPERATURE

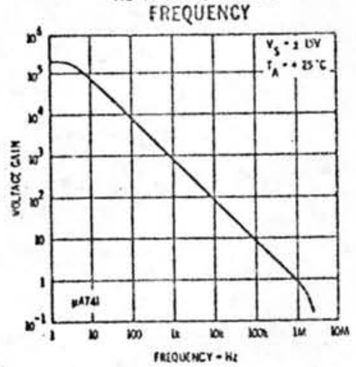


TYPICAL PERFORMANCE CURVES (312 AND 393 GRADES)

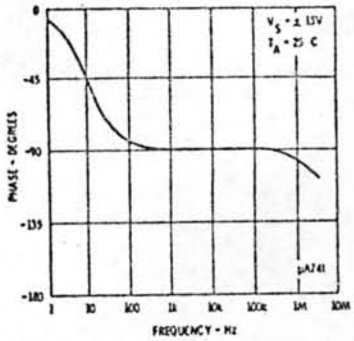
POWER CONSUMPTION AS A FUNCTION OF SUPPLY VOLTAGE



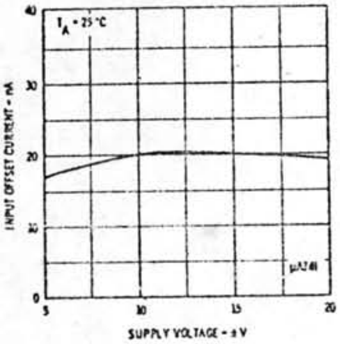
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF FREQUENCY



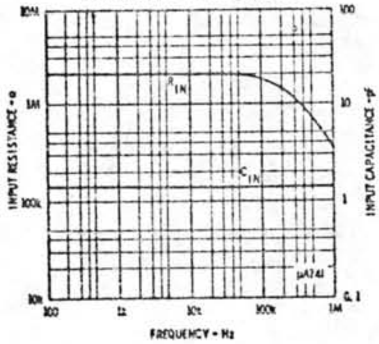
OPEN LOOP PHASE RESPONSE AS A FUNCTION OF FREQUENCY



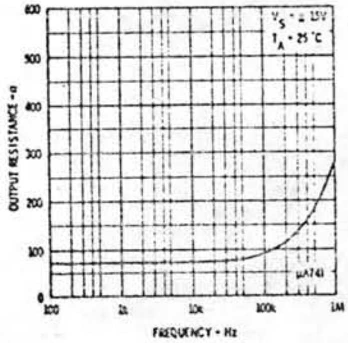
INPUT OFFSET CURRENT AS A FUNCTION OF SUPPLY VOLTAGE



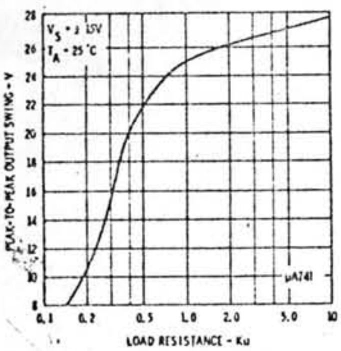
INPUT RESISTANCE AND INPUT CAPACITANCE AS A FUNCTION OF FREQUENCY



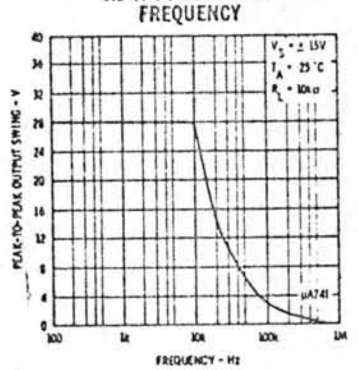
OUTPUT RESISTANCE AS A FUNCTION OF FREQUENCY



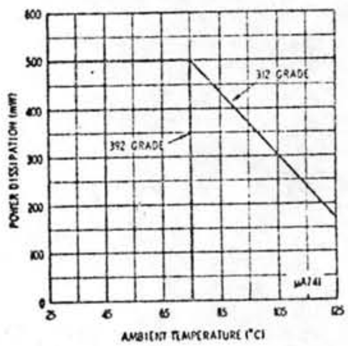
OUTPUT VOLTAGE SWING AS A FUNCTION OF LOAD RESISTANCE



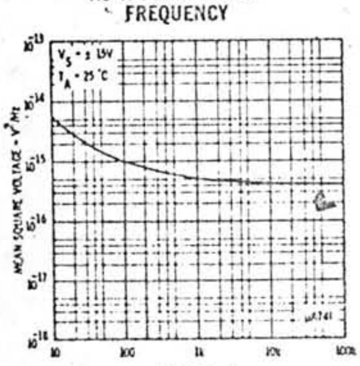
OUTPUT VOLTAGE SWING AS A FUNCTION OF FREQUENCY



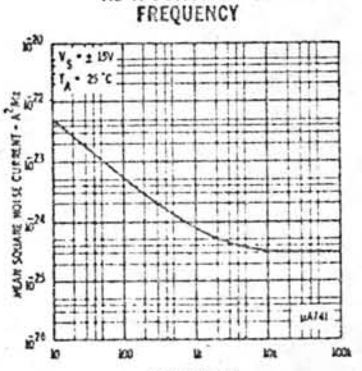
ABSOLUTE MAXIMUM POWER DISSIPATION AS A FUNCTION OF AMBIENT TEMPERATURE



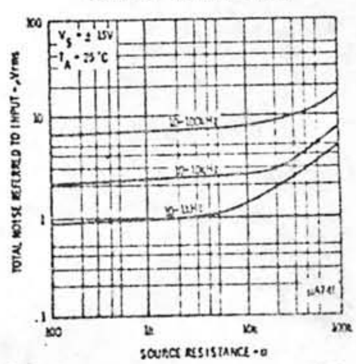
INPUT NOISE VOLTAGE AS A FUNCTION OF FREQUENCY



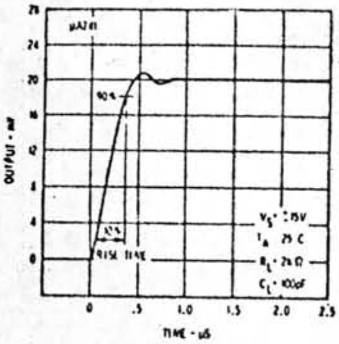
INPUT NOISE CURRENT AS A FUNCTION OF FREQUENCY



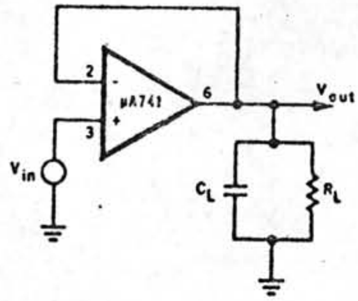
BROADBAND NOISE FOR VARIOUS BANDWIDTHS



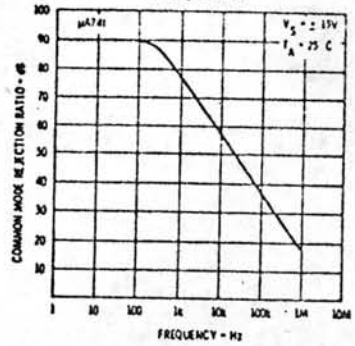
TRANSIENT RESPONSE



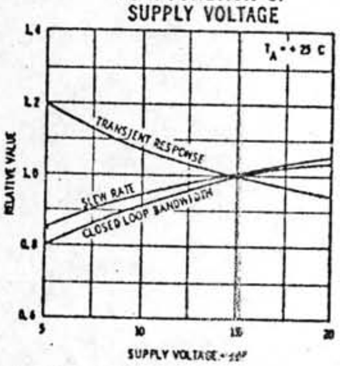
TRANSIENT RESPONSE TEST CIRCUIT



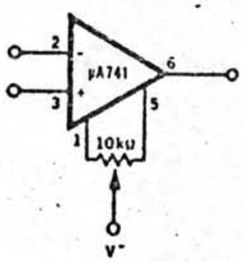
COMMON MODE REJECTION RATIO AS A FUNCTION OF FREQUENCY



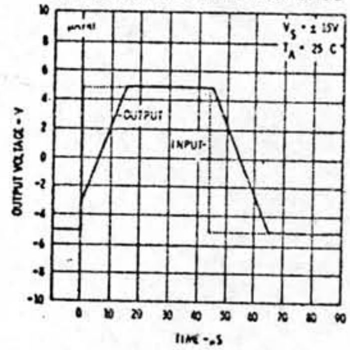
FREQUENCY CHARACTERISTICS AS A FUNCTION OF SUPPLY VOLTAGE



VOLTAGE OFFSET NULL CIRCUIT

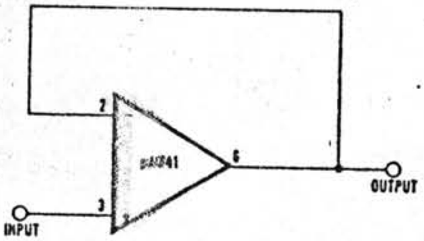


VOLTAGE FOLLOWER LARGE-SIGNAL PULSE RESPONSE



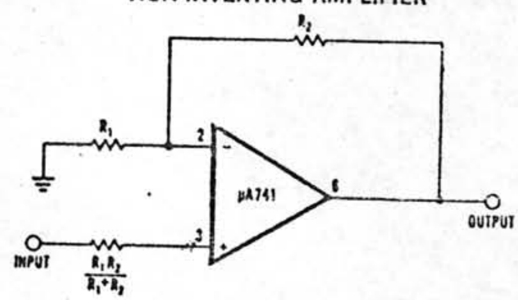
TYPICAL APPLICATIONS

UNITY-GAIN VOLTAGE FOLLOWER



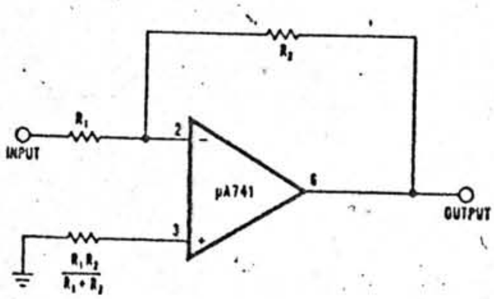
R_{IN} = 400 MΩ
C_{IN} = 1 pF
R_{OUT} << 1 Ω
B.W. = 1 MHz

NON-INVERTING AMPLIFIER



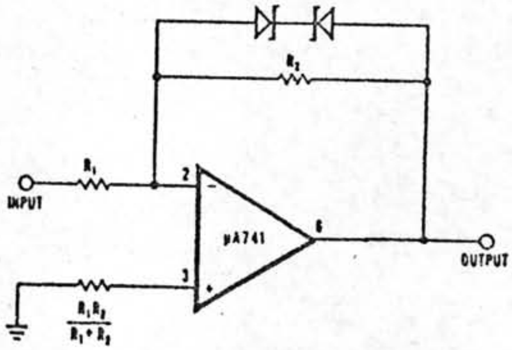
GAIN	R_1	R_2	B.W.	R_{IN}
10	1 kΩ	9 kΩ	100 kHz	400 MΩ
100	100 Ω	9.9 kΩ	10 kHz	280 MΩ
1000	100 Ω	99.9 kΩ	1 kHz	80 MΩ

INVERTING AMPLIFIER



GAIN	R_1	R_2	B.W.	R_{IN}
1	10 kΩ	10 kΩ	1 MHz	10 kΩ
10	1 kΩ	10 kΩ	100 kHz	1 kΩ
100	1 kΩ	100 kΩ	10 kHz	1 kΩ
1000	100 Ω	100 kΩ	1 kHz	100 Ω

CLIPPING AMPLIFIER

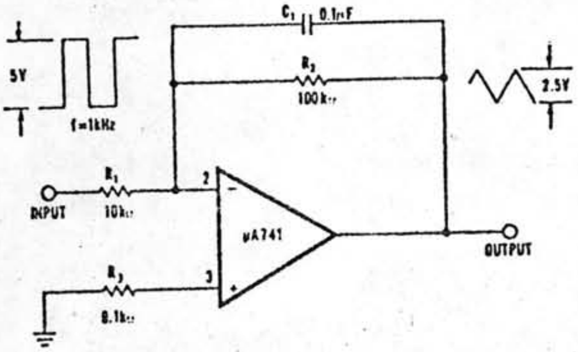


$$\frac{E_{out}}{E_{IN}} = -\frac{R_2}{R_1} \text{ if } |E_{out}| \le V_Z + 0.7$$

where V_Z = Ze

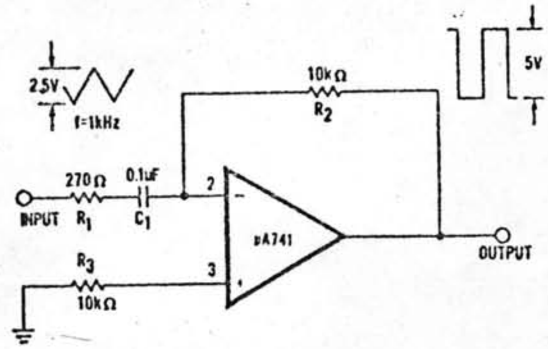
TYPICAL APPLICATIONS

SIMPLE INTEGRATOR



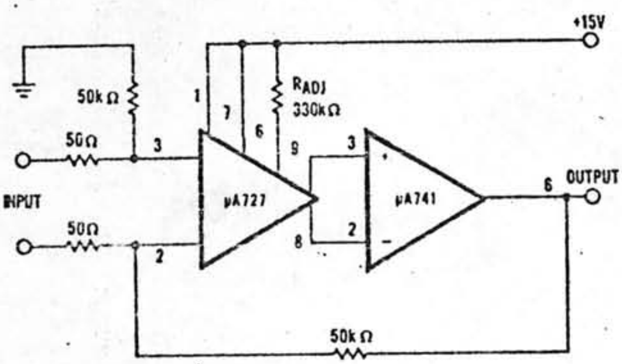
$$E_{out} = -\frac{1}{R_1C_1}\int E_{IN}dt$$

SIMPLE DIFFERENTIATOR



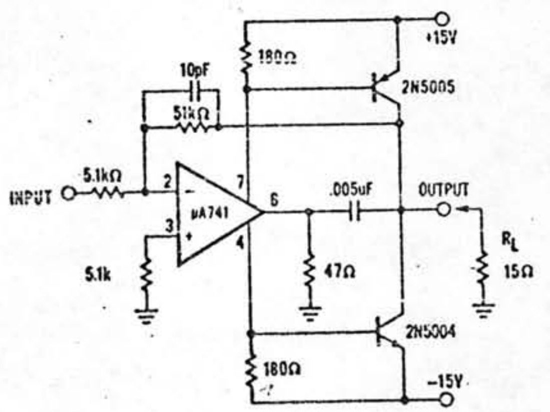
$$E_{out} = -R_2C_1\frac{dE_{IN}}{dt}$$

LOW DRIFT LOW NOISE AMPLIFIER

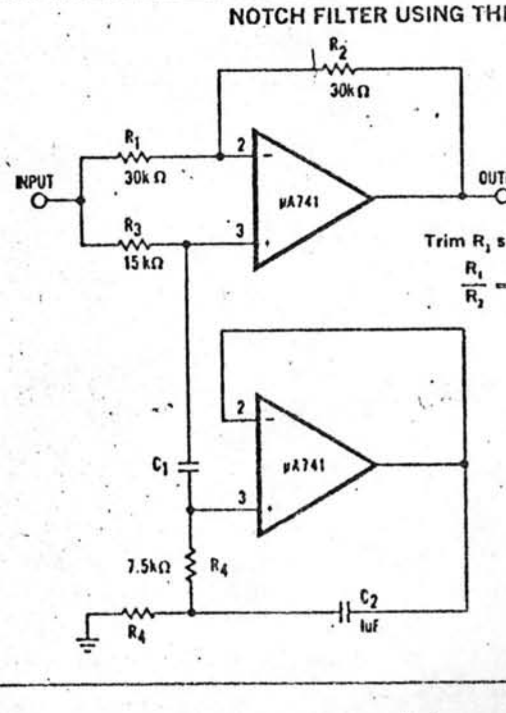


Voltage Gain = 10^3
Input Offset Voltage Drift = 0.6 μV/°C
Input Offset Current Drift = 2.0 pA/°C

HIGH SLEW RATE POWER AMPLIFIER



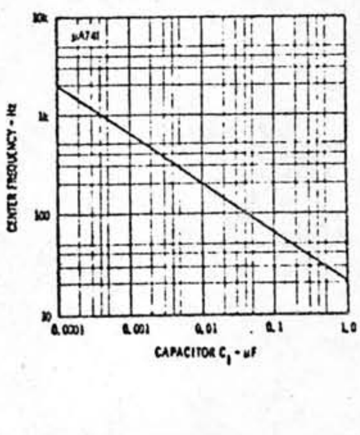
NOTCH FILTER USING THE μA741 AS A GYRATOR



Trim R_3 such that

$$\frac{R_1}{R_2} = \frac{R_3}{2R_4}$$

NOTCH FREQUENCY AS A FUNCTION OF C_1



Operational Amplifiers

Definition of Terms

Input Offset Voltage - That voltage which must be applied between the input terminals to obtain zero output voltage. The input offset voltage may also be defined for the case where two equal resistances are inserted in series with the input leads.

Input Offset Current - The difference in the currents into the two input terminals with the output at zero volts.

Input Resistance - The resistance looking into either input terminal with the other grounded.

Input Bias Current - The average of the two input currents.

Input Voltage Range - The range of voltage , which if exceeded on either input terminal, could cause the amplifier to cease functioning properly.

Input Common Mode Rejection Ratio - The ratio of the input voltage to the maximum change in input offset voltage over this range.

Supply Voltage Rejection Ratio - The ratio of the change in input offset voltage to the change in supply voltage producing it.

Large Signal Voltage Gain - The ratio of the maximum output voltage swing with load to the change in input voltage required to drive the output from zero to this voltage.

Output Voltage Swing - The peak output swing, referred to zero, that can be obtained without clipping.

Output Resistance - The resistance seen looking into the output terminal with the output at null. The parameter is defined only under small signal conditions at frequencies above a few hundred cycles to eliminate the influence of drift and thermal feedback.

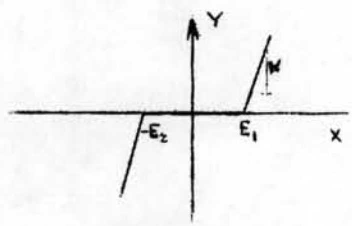
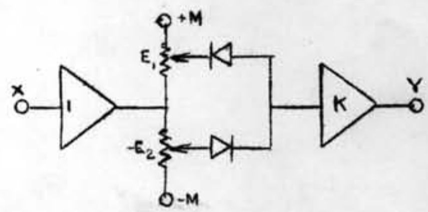
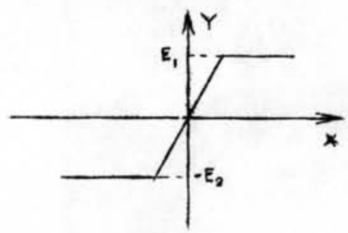
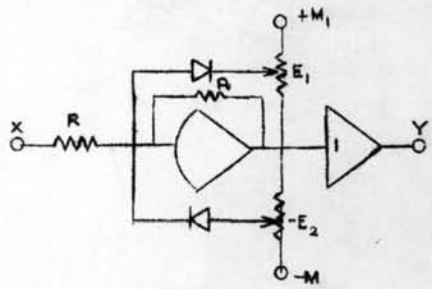
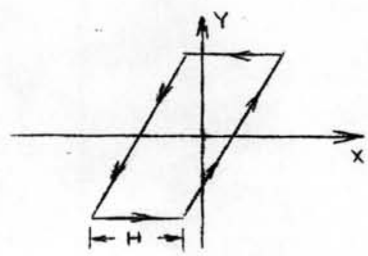
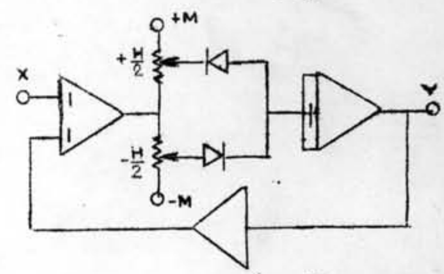
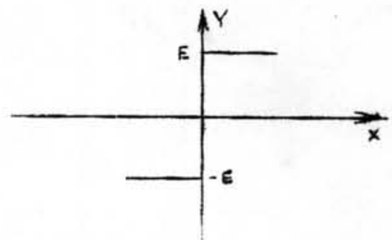
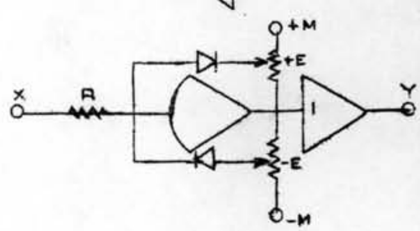
Power Consumption - The D.C. power required to operate the amplifier with the output at zero and with no load current.

Transient Response - The closed-loop step function response of the amplifier under small signal conditions.

Peak Output Current - The maximum current that may flow in the output load without causing damage to the unit.

Appendix B

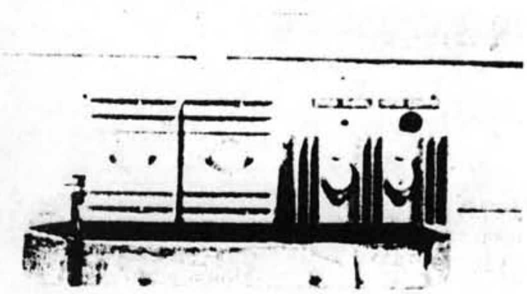
Simulation of Common Nonlinearities

Type of Nonlinearity.	Characteristics	Simulation Circuit
Dead Zone		
Saturation		
Backlash		
Coulomb Friction		

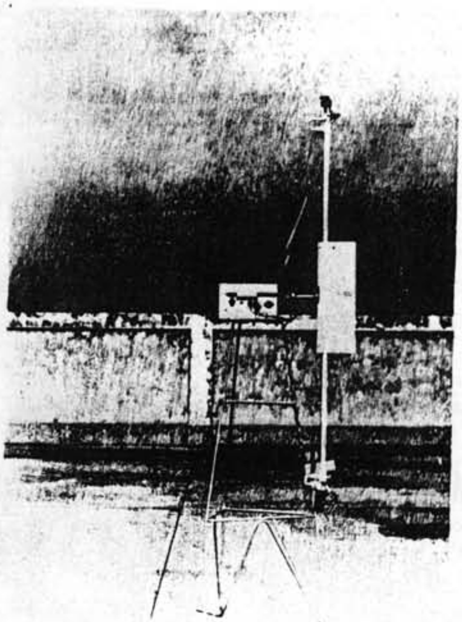
Appendix C

PHOTOGRAPHS OF THE SYSTEMATIC MODEL

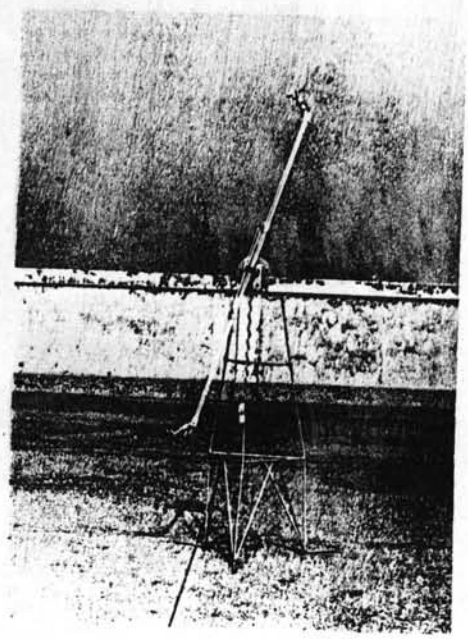
FRONT VIEW OF CONTROLLER



REAR VIEW OF CONTROLLER

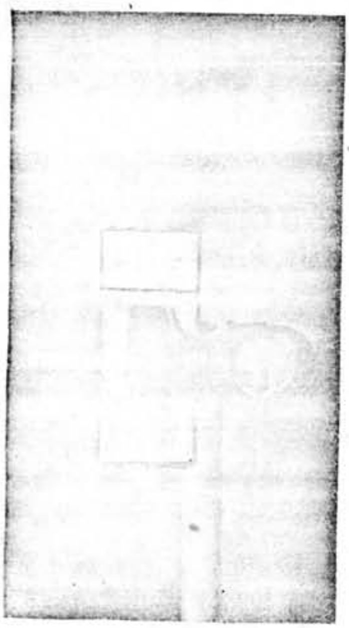


SIDE VIEW OF MOVING CONSTRUCTION

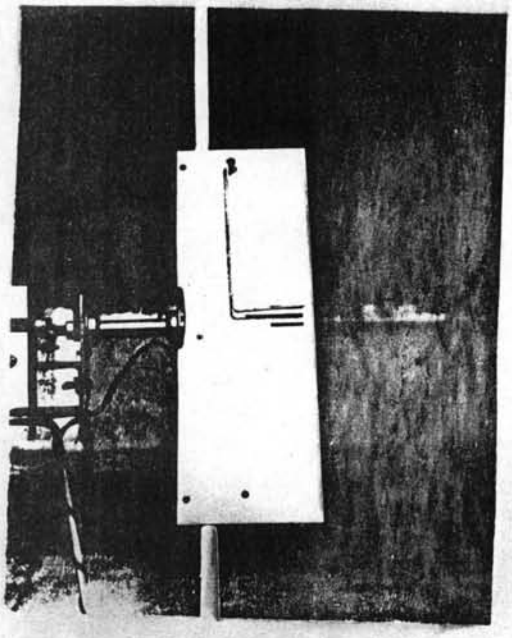


FRONT VIEW OF MOVING CONSTRUCTION

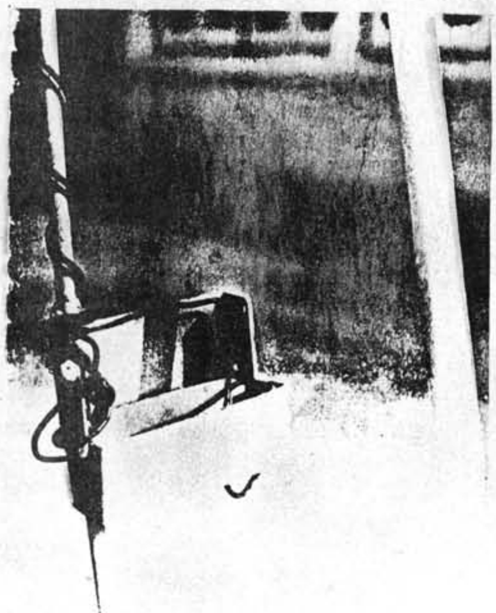
LOCATION OF SOLAR CELL



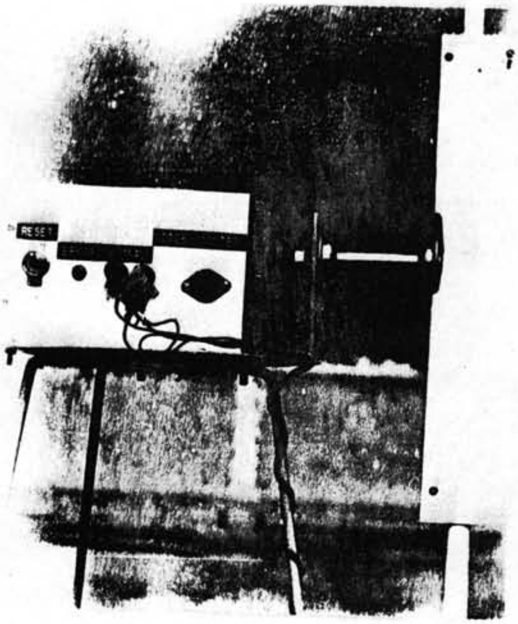
A SOLAR CELL



THE FLAT PLATE

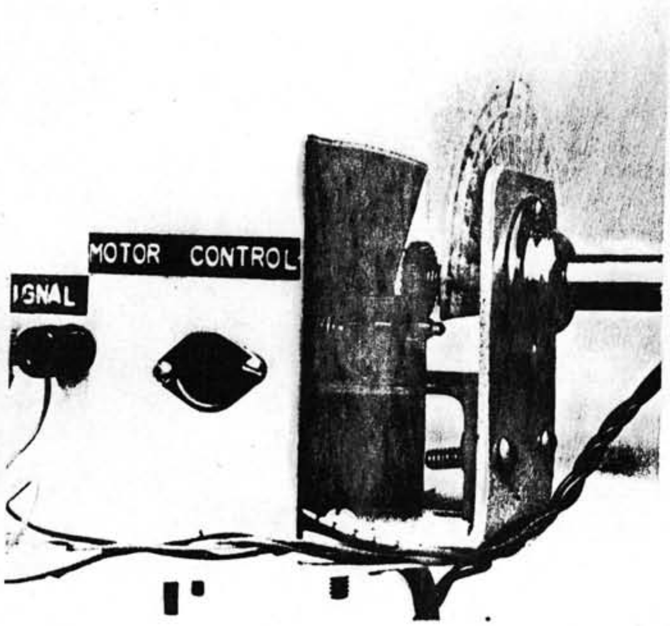


LOCATION OF LIMIT SWITCHES

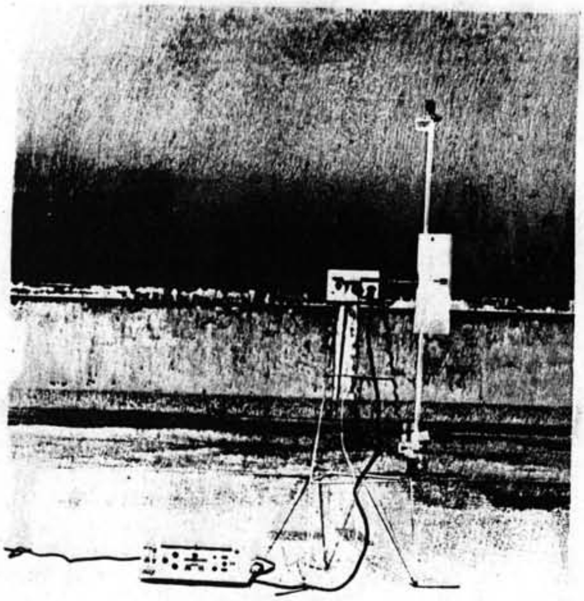


CONTROL TERMINALS OF

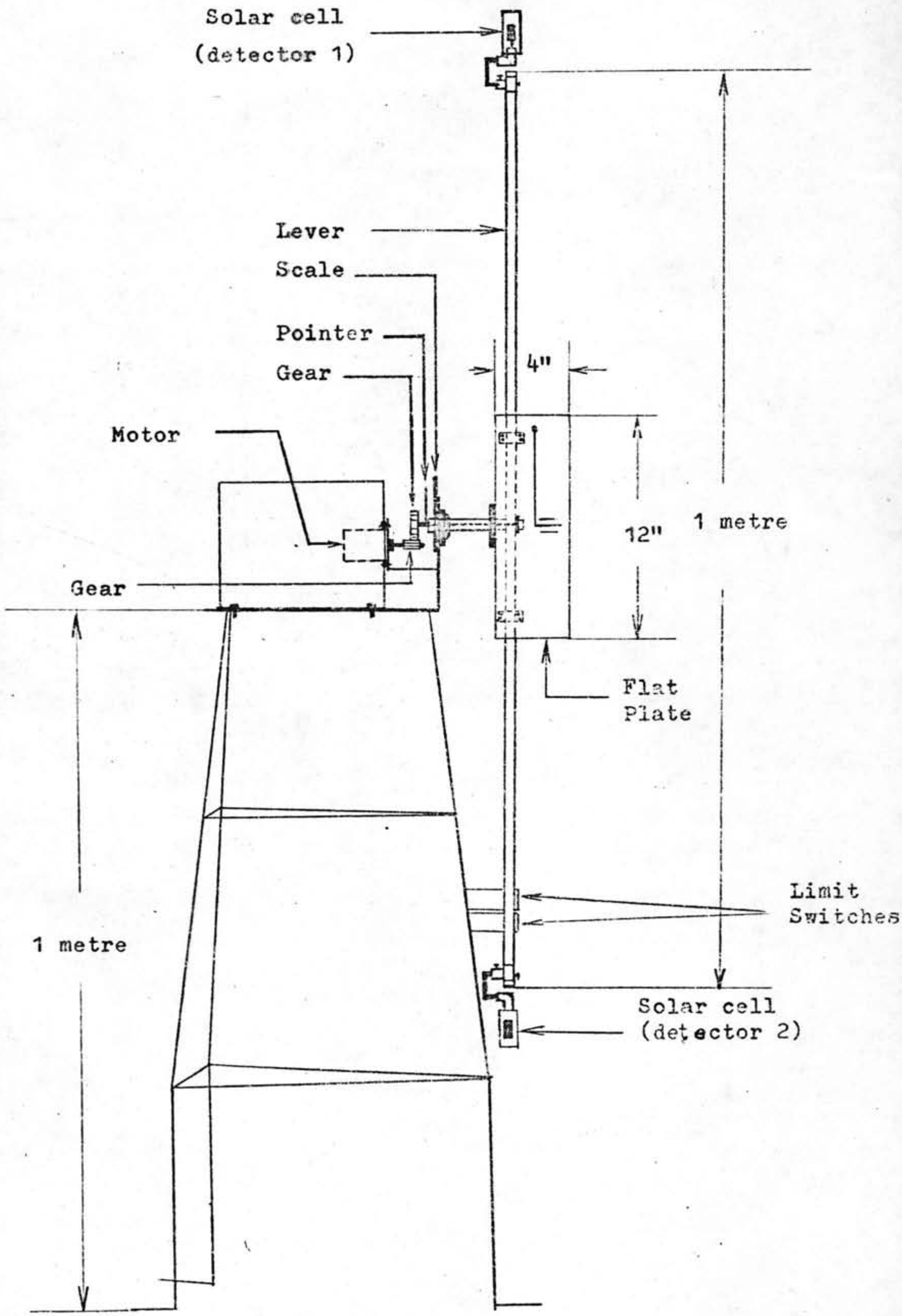
THE MOVING PART



GEAR TRAIN



EXPERIMENTAL SET UP OF SOLAR TRACKING SYSTEM



A PICTURE OF THE MOVING CONSTRUCTION

VITA

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